

Form 1449*	Atty. Docket No.: 303.459US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: Herewith	Group: Unknown

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**Examiner		Document Number	Date	Name	Class	Subclass	Filing Date
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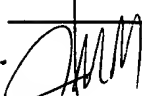
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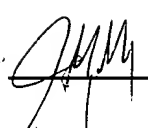

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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.